



Si Photodetector (GT101)



Features:

- High responsivity
- High speed
- Low dark current
- Low capacitance
- Flat window

Applications:

- Optical communications
- Ranging
- Industry automatic control system
- Optical power meter

Absolute maximum ratings

Parameter	Symbol	Value	Unit
Operating temperature	T_{op}	-40~+85	°C
Storage temperature	T_{stg}	-40~+85	°C
Forward current	I_f	10	mA
Reverse current	I_r	1000	μA


Electrical and optical characteristics (T =25°C, V_R =15 V, λ =900 nm)

Parameter	Symbol	Unit	Value				
			0.5	1.0	2.0	4.0	5.0
Active area	φ	mm	0.5	1.0	2.0	4.0	5.0
Spectral range	λ _R	nm	400~1100				
Operating wavelength	λ _P	nm	900±50				
Junction capacitance	C _j	pF	1.2	2	5.5	20	35
Responsivity	R _e	μA/μW	0.5				
Operating voltage	V _R	V	15	3	6	15	20
Dark current	I _D	nA	1.2	2	5	10	25
Response time	t _r	ns	1	3		5	
Operating temperature	T _{OP}	°C	-45~+120				
Package			TO-2	5501	TO-5	TO-8	